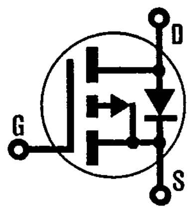
Data Sheet No. PD-9.320F
T-39-21

INTERNATIONAL RECTIFIER IOR

HEXFET® TRANSISTORS IRF9530 IRF9531 IRF9532 IRF9533



P-Channel

TO-220

-100 Volt, 0.3 Ohm HEXFET TO-220AB Plastic Package

The HEXFET® technology is the key to International Rectifier's advanced line of power MOSFET transistors. The efficient geometry and unique processing of the HEXFET design achieve very low on-state resistance combined with high transconductance and extreme device ruggedness.

The P-Channel HEXFETs are designed for applications which require the convenience of reverse polarity operation. They retain all of the features of the more common N-Channel HEXFETs such as voltage control, very fast switching, ease of paralleling, and excellent temperature stability. The P-Channel IRF9530 device is an approximate electrical complement to the N-Channel IRF520 HEXFET.

P-Channel HEXFETs are intended for use in power stages where complementary symmetry with N-Channel devices offers circuit simplification. They are also very useful in drive stages because of the circuit versatility offered by the reverse polarity connection. Applications include motor control, audio amplifiers, switched mode converters, control circuit and pulse amplifiers.

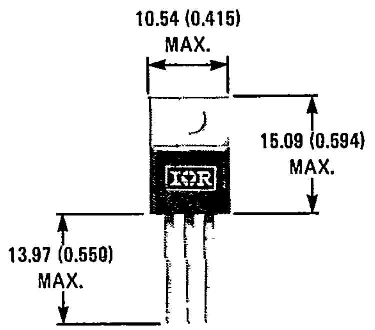
Features:

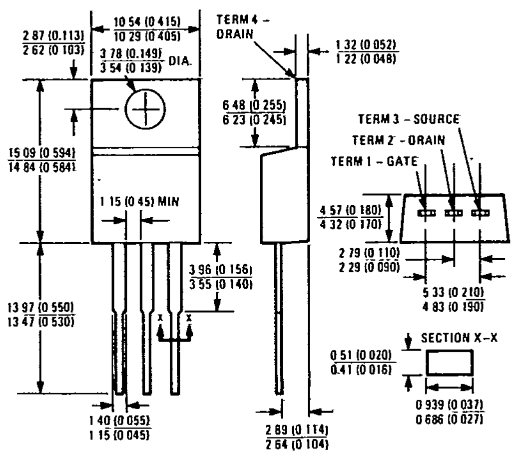
- P-Channel Versatility
- Compact Plastic Package
- Fast Switching
- Low Drive Current
- Ease of Paralleling
- Excellent Temperature Stability

Product Summary

Part Number	V_{DS}	$R_{DS(on)}$	I_D
IRF9530	-100V	0.30Ω	-12A
IRF9531	-60V	0.30Ω	-12A
IRF9532	-100V	0.40Ω	-10A
IRF9533	-60V	0.40Ω	-10A

CASE STYLE AND DIMENSIONS





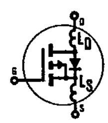
Case Style TO-220AB
Dimensions in Millimeters and (Inches)

IRF9530, IRF9531, IRF9532, IRF9533 Devices

Absolute Maximum Ratings

	Parameter	IRF9530	IRF9531	IRF9532	IRF9533	Units
V_{DS}	Drain - Source Voltage ①	-100	-60	-100	-60	V
V_{DGR}	Drain - Gate Voltage (R_{GS} = 20 kΩ) ①	-100	-60	-100	-60	V
I_D @ T_C = 25°C	Continuous Drain Current	-12	-12	-10	-10	A
I_D @ T_C = 100°C	Continuous Drain Current	-7.5	-7.5	-6.5	-6.5	A
I_{DM}	Pulsed Drain Current ③	-48	-48	-40	-40	A
V_{GS}	Gate - Source Voltage	±20				V
P_D @ T_C = 25°C	Max. Power Dissipation	75 (See Fig. 14)				W
	Linear Derating Factor	0.6 (See Fig. 14)				W/K④
I_{LM}	Inductive Current, Clamped	(See Fig. 15 and 16) L = 100μH -48	-48	-40	-40	A
T_J T_{stg}	Operating Junction and Storage Temperature Range	-55 to 150				°C
	Lead Temperature	300 (0.063 in. (1.6mm) from case for 10s)				°C

Electrical Characteristics @T_C = 25°C (Unless Otherwise Specified)

Parameter		Type	Min.	Typ.	Max.	Units	Test Conditions
BV_{DSS}	Drain - Source Breakdown Voltage	IRF9530 IRF9532	-100	—	—	V	V_{GS} = 0V
		IRF9531 IRF9533	-60	—	—	V	I_D = -250μA
$V_{GS(th)}$	Gate Threshold Voltage	ALL	-2.0	—	-4.0	V	V_{DS} = V_{GS}, I_D = -250μA
I_{GSS}	Gate-Source Leakage Forward	ALL	—	—	-500	nA	V_{GS} = -20V
I_{GSS}	Gate-Source Leakage Reverse	ALL	—	—	500	nA	V_{GS} = 20V
I_{DSS}	Zero Gate Voltage Drain Current	ALL	—	—	-250	μA	V_{DS} = Max. Rating, V_{GS} = 0V
			—	—	-1000	μA	V_{DS} = Max. Rating x 0.8, V_{GS} = 0V, T_C = 125°C
$I_{D(on)}$	On-State Drain Current ②	IRF9530 IRF9531	-12	—	—	A	V_{DS} > $I_{D(on)}$ x $R_{DS(on)}$ max., V_{GS} = -10V
		IRF9532 IRF9533	-10	—	—	A	
$R_{DS(on)}$	Static Drain-Source On-State Resistance ②	IRF9530 IRF9531	—	0.25	0.30	Ω	V_{GS} = -10V, I_D = -6.5A
		IRF9532 IRF9533	—	0.30	0.40	Ω	
g_{fs}	Forward Transconductance ②	ALL	2.0	3.8	—	S (℧)	V_{DS} > $I_{D(on)}$ x $R_{DS(on)}$ max., I_D = -6.5A
C_{iss}	Input Capacitance	ALL	—	500	700	pF	V_{GS} = 0V, V_{DS} = -25V, f = 1.0 MHz See Fig. 10
C_{oss}	Output Capacitance	ALL	—	300	450	pF	
C_{rss}	Reverse Transfer Capacitance	ALL	—	100	200	pF	
$t_{d(on)}$	Turn-On Delay Time	ALL	—	30	60	ns	V_{DD} = 0.5 BV_{DSS}, I_D = -6.5A, Z_o = 50Ω See Fig. 17 (MOSFET switching times are essentially independent of operating temperature.)
t_r	Rise Time	ALL	—	70	140	ns	
$t_{d(off)}$	Turn-Off Delay Time	ALL	—	70	140	ns	
t_f	Fall Time	ALL	—	70	140	ns	
Q_g	Total Gate Charge (Gate-Source Plus Gate-Drain)	ALL	—	25	45	nC	V_{GS} = -15V, I_D = -15A, V_{DS} = 0.8 Max. Rating. See Fig. 18 for test circuit. (Gate charge is essentially independent of operating temperature.)
Q_{gs}	Gate-Source Charge	ALL	—	13	—	nC	
Q_{gd}	Gate-Drain ("Miller") Charge	ALL	—	12	—	nC	
L_D	Internal Drain Inductance	ALL	—	3.5	—	nH	Measured from the contact screw on tab to center of die. — Modified MOSFET symbol showing the internal device inductances. 
			—	4.5	—	nH	Measured from the drain lead, 6mm (0.25 in.) from package to center of die.
L_S	Internal Source Inductance	ALL	—	7.5	—	nH	Measured from the source lead, 6mm (0.25 in.) from package to source bonding pad.

Thermal Resistance

R_{thJC}	Junction-to-Case	ALL	—	—	1.67	K/W④	
R_{thCS}	Case-to-Sink	ALL	—	1.0	—	K/W④	Mounting surface flat, smooth, and greased.
R_{thJA}	Junction-to-Ambient	ALL	—	—	80	K/W④	Typical socket mount

IRF9530, IRF9531, IRF9532, IRF9533 Devices

Source-Drain Diode Ratings and Characteristics

Symbol	Parameter	Type	Min.	Typ.	Max.	Units	Test Conditions
I_S	Continuous Source Current (Body Diode)	IRF9530 IRF9531	—	—	-12	A	Modified MOSFET symbol showing the integral reverse P-N junction rectifier. 
		IRF9532 IRF9533	—	—	-10	A	
I_{SM}	Pulse Source Current (Body Diode) ③	IRF9530 IRF9531	—	—	-48	A	
		IRF9532 IRF9533	—	—	-40	A	
V_{SD}	Diode Forward Voltage ②	IRF9530 IRF9531	—	—	-6.3	V	$T_C = 25°C, I_S = -12A, V_{GS} = 0V$
		IRF9532 IRF9533	—	—	-6.0	V	$T_C = 25°C, I_S = -10A, V_{GS} = 0V$
t_{rr}	Reverse Recovery Time	ALL	—	300	—	ns	$T_J = 150°C, I_F = -12A, dI_F/dt = 100 A/\mu s$
Q_{RR}	Reverse Recovered Charge	ALL	—	1.8	—	μC	$T_J = 150°C, I_F = -12A, dI_F/dt = 100 A/\mu s$
t_{on}	Forward Turn-on Time	ALL	Intrinsic turn-on time is negligible. Turn-on speed is substantially controlled by $L_S + L_D$.				

① T_J = 25°C to 150°C. ② Pulse Test: Pulse width ≤ 300μs, Duty Cycle ≤ 2%. ③ Repetitive Rating: Pulse width limited by max. junction temperature. See Transient Thermal Impedance Curve (Fig. 5).

④ K/W = °C/W
W/K = W/°C

TO-220

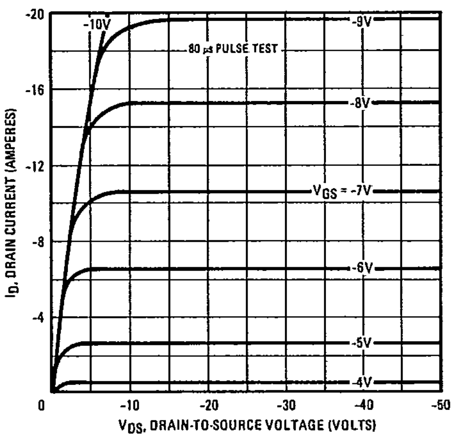


Fig. 1 — Typical Output Characteristics

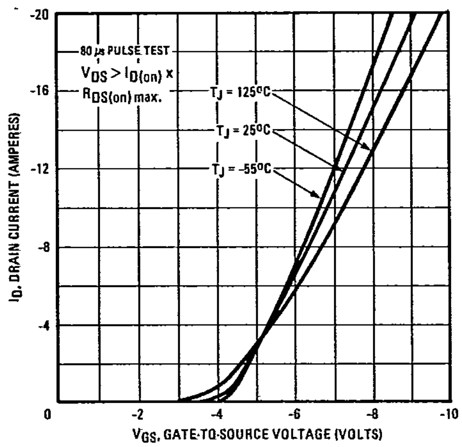


Fig. 2 — Typical Transfer Characteristics

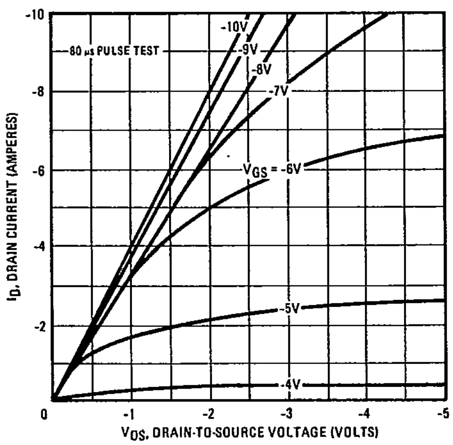


Fig. 3 — Typical Saturation Characteristics

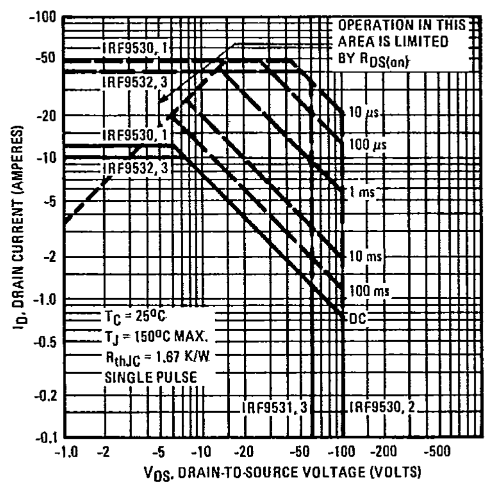


Fig. 4 — Maximum Safe Operating Area

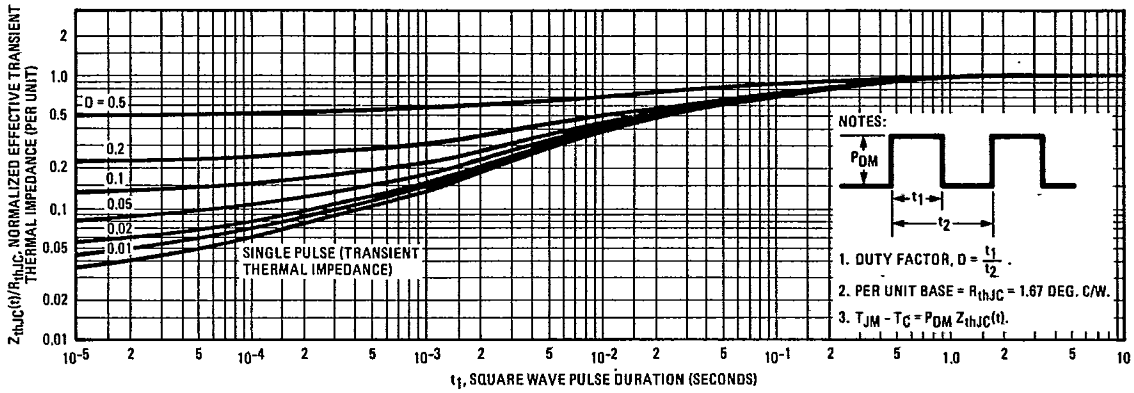


Fig. 5 — Maximum Effective Transient Thermal Impedance, Junction-to-Case Vs. Pulse Duration

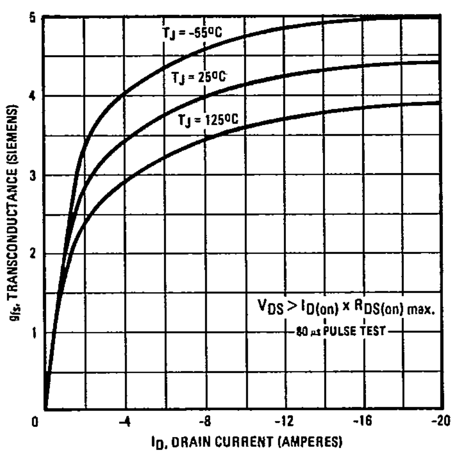


Fig. 6 — Typical Transconductance Vs. Drain Current

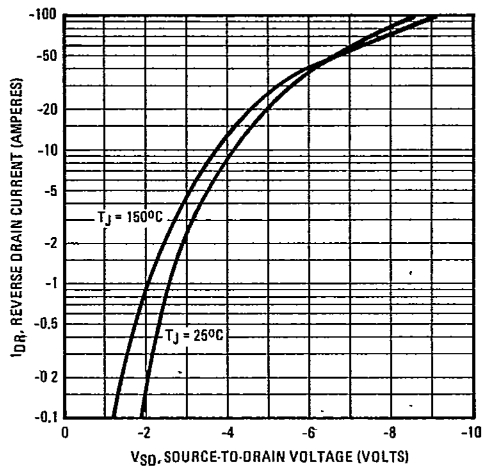


Fig. 7 — Typical Source-Drain Diode Forward Voltage

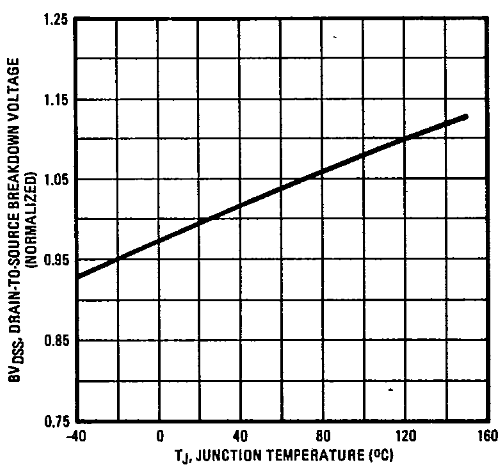


Fig. 8 — Breakdown Voltage Vs. Temperature

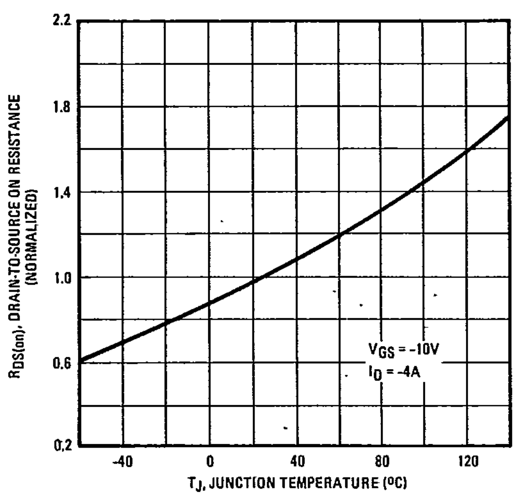


Fig. 9 — Normalized On-Resistance Vs. Temperature

IRF9530, IRF9531, IRF9532, IRF9533 Devices

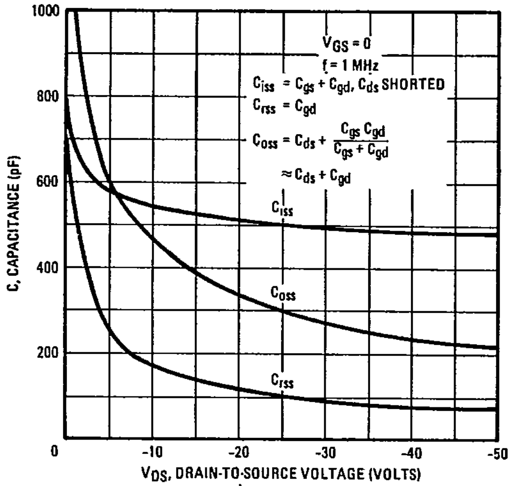


Fig. 10 — Typical Capacitance Vs. Drain-to-Source Voltage

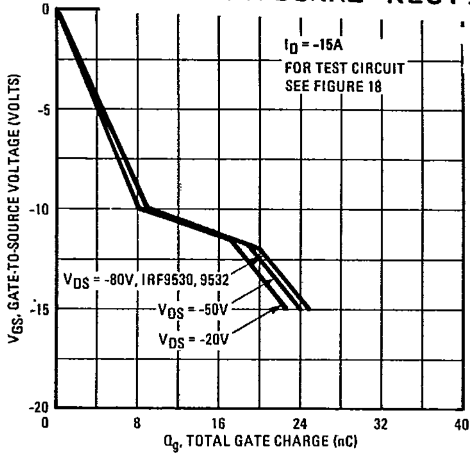


Fig. 11 — Typical Gate Charge Vs. Gate-to-Source Voltage

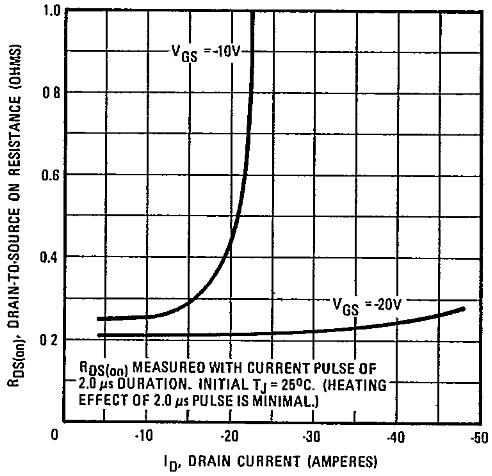


Fig. 12 — Typical On-Resistance Vs. Drain Current

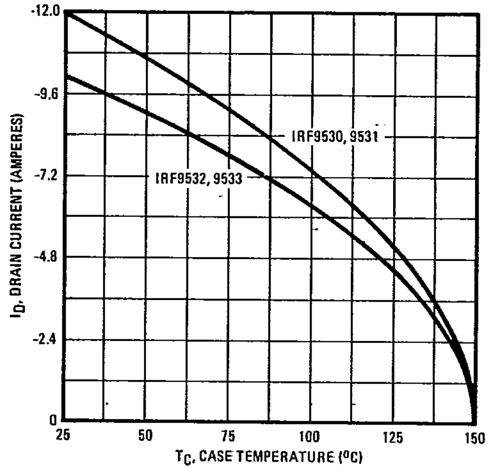


Fig. 13 — Maximum Drain Current Vs. Case Temperature

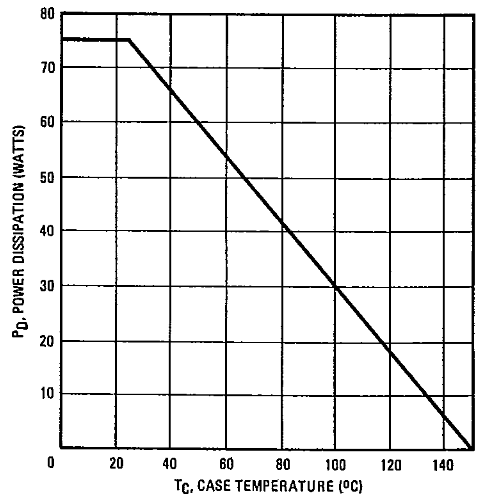


Fig. 14 — Power Vs. Temperature Derating Curve

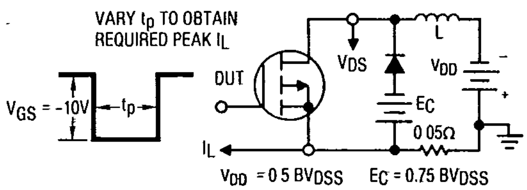


Fig. 15 — Clamped Inductive Test Circuit

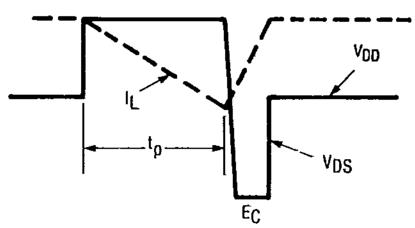


Fig. 16 — Clamped Inductive Waveforms

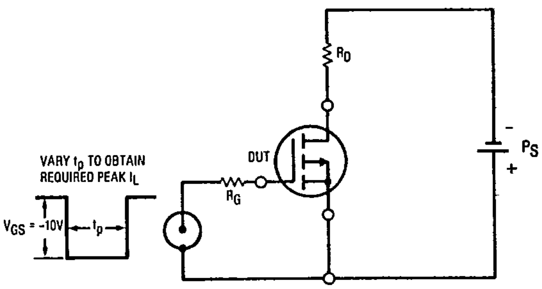


Fig. 17 – Switching Time Test Circuit

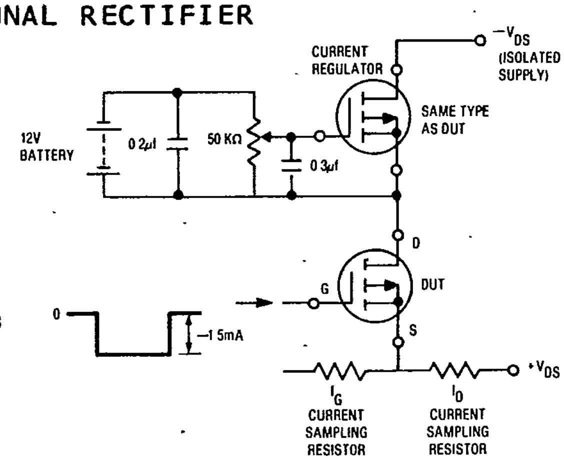


Fig. 18 – Gate Charge Test Circuit

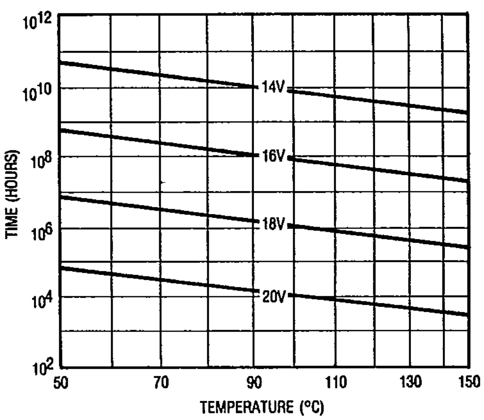


*Fig. 19 – Typical Time to Accumulated 1% Failure

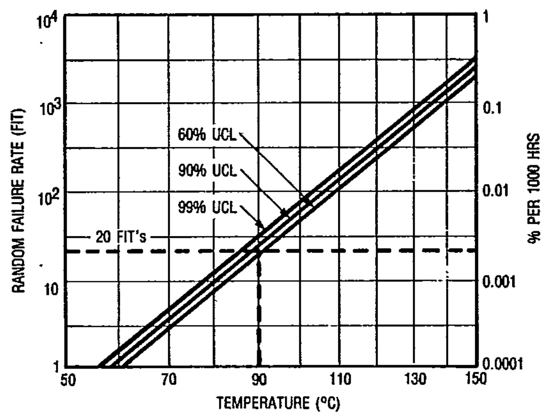


*Fig. 20 – Typical High Temperature Reverse Bias (HTRB) Failure Rate

*The data shown is correct as of April 15, 1987. This information is updated on a quarterly basis; for the latest reliability data, please contact your local IR field office.